

# Robert Kudrawiec

## List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

315  
papers

4,227  
citations

32  
h-index

43  
g-index

340  
ext. papers

4,808  
ext. citations

3.1  
avg, IF

5.56  
L-index

#	Paper	IF	Citations
315	Radiative and nonradiative recombination processes in GaNP(As) alloys. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2022</b> , 276, 115567	3.1	
314	Photoreflectance studies of temperature and hydrostatic pressure dependencies of direct optical transitions in BGaAs alloys grown on GaP. <i>Journal Physics D: Applied Physics</i> , <b>2022</b> , 55, 015107	3	1
313	Probing the long-lived photo-generated charge carriers in transition metal dichalcogenides by time-resolved microwave photoconductivity. <i>Nanophotonics</i> , <b>2022</b> , 11, 1335-1344	6.3	1
312	Temperature Dependence of the Indirect Gap and the Direct Optical Transitions at the High-Symmetry Point of the Brillouin Zone and Band Nesting in MoS, MoSe, MoTe, WS, and WSe Crystals.. <i>Journal of Physical Chemistry C</i> , <b>2022</b> , 126, 5665-5674	3.8	1
311	Detailed surface studies on the reduction of Al incorporation into AlGaIn grown by molecular beam epitaxy in the Ga-droplet regime. <i>Vacuum</i> , <b>2022</b> , 111168	3.7	0
310	Thermal oxidation of [0001] GaN in water vapor compared with dry and wet oxidation: Oxide properties and impact on GaN. <i>Applied Surface Science</i> , <b>2022</b> , 598, 153872	6.7	0
309	The influence of the photovoltaic effect on the surface electric field in GaN. <i>Applied Surface Science</i> , <b>2021</b> , 151905	6.7	1
308	Modified band alignment method to obtain hybrid functional accuracy from standard DFT: Application to defects in highly mismatched III-V:Bi alloys. <i>Physical Review Materials</i> , <b>2021</b> , 5,	3.2	1
307	Influence of pulsed Al deposition on quality of Al-rich Al(Ga)N structures grown by molecular beam epitaxy. <i>Surfaces and Interfaces</i> , <b>2021</b> , 27, 101560	4.1	1
306	The effect of isovalent doping on the electronic band structure of group IV semiconductors. <i>Journal Physics D: Applied Physics</i> , <b>2021</b> , 54, 085102	3	
305	Green Solvent-Based Perovskite Precursor Development for Ink-Jet Printed Flexible Solar Cells. <i>ACS Sustainable Chemistry and Engineering</i> , <b>2021</b> , 9, 3920-3930	8.3	9
304	Mask-free three-dimensional epitaxial growth of III-nitrides. <i>Journal of Materials Science</i> , <b>2021</b> , 56, 558-569	4.9	2
303	Electronic band structure of semiconductor alloys: From ab initio to k $\cdot$ p via computational alchemy, on example of Ge <sub>1-x</sub> Sn <sub>x</sub> alloy. <i>Computational Materials Science</i> , <b>2021</b> , 187, 110052	3.2	2
302	Arsenic-Induced Growth of Dodecagonal GaN Microrods with Stable a-Plane Walls. <i>Advanced Optical Materials</i> , <b>2021</b> , 9, 2001348	8.1	3
301	Contactless electroreflectance spectroscopy with a semitransparent capacitor made of a silver mesh of ultrathin lines. <i>Measurement: Journal of the International Measurement Confederation</i> , <b>2021</b> , 169, 108361	4.6	2
300	Electric Fields and Surface Fermi Level in Undoped GaN/AlN Two-Dimensional Hole Gas Heterostructures. <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2021</b> , 15, 2000573	2.5	2
299	Experimental and Theoretical Studies of the Electronic Band Structure of Bulk and Atomically Thin Mo W Se Alloys. <i>ACS Omega</i> , <b>2021</b> , 6, 19893-19900	3.9	3

298	Band engineering in nitrogen-rich AlGaNs quaternary alloys. <i>Vacuum</i> , <b>2021</b> , 189, 110240	3.7	
297	Carrier Dynamics in Thin Germanium $\pi$ in Epilayers. <i>ACS Applied Electronic Materials</i> , <b>2021</b> , 3, 344-352	4	1
296	Bandgap engineering in III-nitrides with boron and group V elements: Toward applications in ultraviolet emitters. <i>Applied Physics Reviews</i> , <b>2020</b> , 7, 041314	17.3	11
295	Boron influence on bandgap and photoluminescence in B GaN grown on AlN. <i>Journal of Applied Physics</i> , <b>2020</b> , 127, 165703	2.5	7
294	Valley polarization investigation of GeS under high pressure. <i>Physical Review B</i> , <b>2020</b> , 101,	3.3	3
293	Optical Gain Characteristics of B GaAs/GaP Quantum Wells. <i>IEEE Photonics Journal</i> , <b>2020</b> , 12, 1-13	1.8	2
292	Inhomogeneous broadening of optical transitions observed in photoluminescence and modulated reflectance of polar and non-polar InGaN quantum wells. <i>Journal of Applied Physics</i> , <b>2020</b> , 127, 035702	2.5	1
291	Determination of dislocation density in GaN/sapphire layers using XRD measurements carried out from the edge of the sample. <i>Journal of Alloys and Compounds</i> , <b>2020</b> , 825, 153838	5.7	10
290	Hidden spin-polarized bands in semiconducting 2H-MoTe <sub>2</sub> . <i>Materials Research Letters</i> , <b>2020</b> , 8, 75-81	7.4	11
289	Combined Temperature and Pressure Sensing Using Luminescent NaBiF <sub>4</sub> :Yb,Er Nanoparticles. <i>ACS Applied Nano Materials</i> , <b>2020</b> , 3, 4209-4217	5.6	38
288	Sn 5s <sub>2</sub> lone pairs and the electronic structure of tin sulphides: A photoreflectance, high-energy photoemission, and theoretical investigation. <i>Physical Review Materials</i> , <b>2020</b> , 4,	3.2	4
287	Optical gain sensitivity of B GaAs/GaP quantum wells to admixtures of group III and V atoms. <i>Optical Materials Express</i> , <b>2020</b> , 10, 2962	2.6	4
286	Temperature-dependent study of GaAs <sub>1-x</sub> N <sub>x</sub> Bi <sub>y</sub> alloys for band-gap engineering: photoreflectance and k $\cdot$ p modeling. <i>Applied Physics Express</i> , <b>2020</b> , 13, 091005	2.4	2
285	Exfoliated CrPS with Promising Photoconductivity. <i>Small</i> , <b>2020</b> , 16, e1905924	11	19
284	Optical properties and dynamics of excitons in Ga(Sb, Bi)/GaSb quantum wells: evidence for a regular alloy behavior. <i>Semiconductor Science and Technology</i> , <b>2020</b> , 35, 025024	1.8	1
283	Determination of Fermi Level Position at the Graphene/GaN Interface Using Electromodulation Spectroscopy. <i>Advanced Materials Interfaces</i> , <b>2020</b> , 7, 2001220	4.6	3
282	SiN/(Al,Ga)N interface barrier in N-polar III-nitride transistor structures studied by modulation spectroscopy. <i>Scientific Reports</i> , <b>2020</b> , 10, 12099	4.9	0
281	New Synthetic Route of Ultrapure Alkylammonium Iodides for Perovskite Thin Films of Superior Optoelectronic Properties. <i>Energy Technology</i> , <b>2020</b> , 8, 2000478	3.5	2

280	Anisotropic optical properties of GeS investigated by optical absorption and photoreflectance. <i>Materials Advances</i> , <b>2020</b> , 1, 1886-1894	3.3	6
279	Towards band gap engineering via biaxial and axial strain in group IV crystals. <i>Computational Materials Science</i> , <b>2020</b> , 181, 109729	3.2	1
278	As-related stability of the band gap temperature dependence in N-rich GaNAs. <i>Applied Physics Letters</i> , <b>2019</b> , 115, 092106	3.4	5
277	Phase-Transition-Induced Carrier Mass Enhancement in 2D Ruddlesden-Popper Perovskites. <i>ACS Energy Letters</i> , <b>2019</b> , 4, 2386-2392	20.1	25
276	Mapping the composition-dependence of the energy bandgap of GaAsN <sub>x</sub> Bi alloys. <i>Applied Physics Letters</i> , <b>2019</b> , 115, 082106	3.4	4
275	Effects of the host conduction band energy on the electronic band structure of ZnCdTeO dilute oxide alloys. <i>Journal of Applied Physics</i> , <b>2019</b> , 126, 083106	2.5	2
274	Electronic structure of B <sub>x</sub> Ga <sub>1-x</sub> As alloys using hybrid functionals. <i>Journal of Applied Physics</i> , <b>2019</b> , 126, 095703	2.5	7
273	Exciton Binding Energy of Two-Dimensional Highly Luminescent Colloidal Nanostructures Determined from Combined Optical and Photoacoustic Spectroscopies. <i>Journal of Physical Chemistry Letters</i> , <b>2019</b> , 10, 3459-3464	6.4	17
272	Type I GaSb <sub>1-x</sub> Bi <sub>x</sub> /GaSb quantum wells dedicated for mid infrared laser applications: Photoreflectance studies of bandgap alignment. <i>Journal of Applied Physics</i> , <b>2019</b> , 125, 205706	2.5	13
271	Study of delocalized and localized states in ZnSeO layers with photoluminescence, micro-photoluminescence, and time-resolved photoluminescence. <i>Journal of Applied Physics</i> , <b>2019</b> , 125, 205702	2.5	3
270	On intrinsic Stokes shift in wide GaN/AlGa <sub>x</sub> N polar quantum wells. <i>Semiconductor Science and Technology</i> , <b>2019</b> , 34, 075021	1.8	1
269	Optical Properties of InGaO Nanowires Revealed by Photoacoustic Spectroscopy. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2019</b> , 11, 19260-19266	9.5	5
268	Pressure dependence of direct optical transitions in ReS <sub>2</sub> and ReSe <sub>2</sub> . <i>Npj 2D Materials and Applications</i> , <b>2019</b> , 3,	8.8	24
267	Strain engineering of transverse electric and transverse magnetic mode of material gain in GeSn/SiGeSn quantum wells. <i>Scientific Reports</i> , <b>2019</b> , 9, 3316	4.9	4
266	Stability of the intermediate band energy position upon temperature changes in GaNP and GaNPAs. <i>Solar Energy Materials and Solar Cells</i> , <b>2019</b> , 196, 131-137	6.4	6
265	Direct and indirect optical transitions in bulk and atomically thin MoS <sub>2</sub> studied by photoreflectance and photoacoustic spectroscopy. <i>Journal of Applied Physics</i> , <b>2019</b> , 125, 135701	2.5	12
264	Photoreflectance and photoinduced microwave reflectance studies of surface band bending in Mg-doped InN. <i>Journal of Applied Physics</i> , <b>2019</b> , 126, 045712	2.5	3
263	Band gap renormalization in n-type GeSn alloys made by ion implantation and flash lamp annealing. <i>Journal of Applied Physics</i> , <b>2019</b> , 125, 203105	2.5	6

262	Supercontinuum source as a probing beam in photoreflectance and photoacoustic spectroscopy. <i>Measurement: Journal of the International Measurement Confederation</i> , <b>2019</b> , 146, 879-884	4.6	
261	Beyond Quantum Efficiency Limitations Originating from the Piezoelectric Polarization in Light-Emitting Devices. <i>ACS Photonics</i> , <b>2019</b> , 6, 1963-1971	6.3	16
260	Electromodulation spectroscopy of highly mismatched alloys. <i>Journal of Applied Physics</i> , <b>2019</b> , 126, 141103	10.3	12
259	Electronic band structure of nitrogen diluted Ga(PAsN): Formation of the intermediate band, direct and indirect optical transitions, and localization of states. <i>Journal of Applied Physics</i> , <b>2019</b> , 126, 175701	2.5	4
258	Material Gain Engineering in Staggered Polar AlGa <sub>N</sub> /AlN Quantum Wells Dedicated for Deep UV Lasers. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , <b>2019</b> , 25, 1-8	3.8	1
257	Verification of threading dislocations density estimation methods suitable for efficient structural characterization of Al <sub>x</sub> Ga <sub>1-x</sub> N/GaN heterostructures grown by MOVPE. <i>Journal of Applied Physics</i> , <b>2019</b> , 126, 165304	2.5	4
256	Bowing of the band gap and spin-orbit splitting energy in BGaAs. <i>Materials Research Express</i> , <b>2019</b> , 6, 125913	1.7	5
255	Depletion Layer Built-In Field at (1 $\bar{1}$ 00), (0001), and (000 $\bar{1}$ ) GaN/Water Junction and Its Role in Semiconductor Nanowire Water Splitting. <i>Advanced Materials Interfaces</i> , <b>2019</b> , 6, 1801497	4.6	
254	Sensitivity of N-polar GaN surface barrier to ambient gases. <i>Sensors and Actuators B: Chemical</i> , <b>2019</b> , 281, 561-567	8.5	5
253	Direct evidence of photoluminescence broadening enhancement by local electric field fluctuations in polar InGa <sub>N</sub> /Ga <sub>N</sub> quantum wells. <i>Japanese Journal of Applied Physics</i> , <b>2018</b> , 57, 020305	1.4	3
252	Emission and material gain spectra of polar compressive strained AlGa <sub>N</sub> quantum wells grown on virtual AlGa <sub>N</sub> substrates: Tuning emission wavelength and mixing TE and TM mode of light polarization. <i>Semiconductor Science and Technology</i> , <b>2018</b> , 33, 075003	1.8	4
251	Contactless electroreflectance study of the surface potential barrier in n-type and p-type InAlAs van Hoof structures lattice matched to InP. <i>Journal Physics D: Applied Physics</i> , <b>2018</b> , 51, 215104	3	2
250	Determination of the band gap of indium-rich InGa <sub>N</sub> by means of photoacoustic spectroscopy. <i>Semiconductor Science and Technology</i> , <b>2018</b> , 33, 035007	1.8	5
249	Structural and optical properties of GaSbBi/GaSb quantum wells [Invited]. <i>Optical Materials Express</i> , <b>2018</b> , 8, 893	2.6	13
248	Zn acceptor position in GaN:Zn probed by contactless electroreflectance spectroscopy. <i>Applied Physics Letters</i> , <b>2018</b> , 113, 032109	3.4	6
247	Temperature dependence of band gaps in dilute bismides. <i>Semiconductor Science and Technology</i> , <b>2018</b> , 33, 073001	1.8	9
246	Strain and Band-Gap Engineering in Ge-Sn Alloys via P Doping. <i>Physical Review Applied</i> , <b>2018</b> , 10,	4.3	10
245	Photoreflectance studies of optical transitions in GaNPAs intermediate band solar cell absorbers. <i>Solar Energy Materials and Solar Cells</i> , <b>2018</b> , 188, 99-104	6.4	4

244	Band gap temperature-dependence of close-space sublimation grown Sb <sub>2</sub> Se <sub>3</sub> by photo-reflectance. <i>APL Materials</i> , <b>2018</b> , 6, 084901	5.7	45
243	Fermi level and bands offsets determination in insulating (Ga,Mn)N/GaN structures. <i>Scientific Reports</i> , <b>2017</b> , 7, 41877	4.9	17
242	The electronic band structure of Ge <sub>1-x</sub> Sn <sub>x</sub> in the full composition range: indirect, direct, and inverted gaps regimes, band offsets, and the Burstein-Moss effect. <i>Journal Physics D: Applied Physics</i> , <b>2017</b> , 50, 195103	3	52
241	Multicolor emission from intermediate band semiconductor ZnOSe. <i>Scientific Reports</i> , <b>2017</b> , 7, 44214	4.9	11
240	Contactless electroreflectance studies of the Fermi level position at the air/GaN interface: Bistable nature of the Ga-polar surface. <i>Applied Surface Science</i> , <b>2017</b> , 396, 1657-1666	6.7	19
239	Effects of band anticrossing on the temperature dependence of the band gap of ZnSe <sub>1-x</sub> O <sub>x</sub> alloys. <i>Semiconductor Science and Technology</i> , <b>2017</b> , 32, 015005	1.8	5
238	Deep-level defects in n-type GaAsBi alloys grown by molecular beam epitaxy at low temperature and their influence on optical properties. <i>Scientific Reports</i> , <b>2017</b> , 7, 12824	4.9	17
237	Transparency of Semi-Insulating, n-Type, and p-Type Ammonothermal GaN Substrates in the Near-Infrared, Mid-Infrared, and THz Spectral Range. <i>Crystals</i> , <b>2017</b> , 7, 187	2.3	9
236	Indium-incorporation enhancement of photoluminescence properties of Ga(In)SbBi alloys. <i>Journal Physics D: Applied Physics</i> , <b>2017</b> , 50, 375102	3	7
235	Nitrogen-related intermediate band in P-rich GaNPAs alloys. <i>Scientific Reports</i> , <b>2017</b> , 7, 15703	4.9	11
234	Photoacoustic and modulated reflectance studies of indirect and direct band gap in van der Waals crystals. <i>Scientific Reports</i> , <b>2017</b> , 7, 15365	4.9	28
233	Electromodulation spectroscopy of heavy-hole, light-hole, and spin-orbit transitions in GaAsBi layers at hydrostatic pressure. <i>Applied Physics Letters</i> , <b>2017</b> , 111, 192104	3.4	7
232	Quasi-ordering of composition fluctuations and their interaction with lattice imperfections in an optical spectra of dilute nitride alloys. <i>Semiconductor Science and Technology</i> , <b>2016</b> , 31, 095012	1.8	6
231	Surface potential barrier in-plane GaN studied by contactless electroreflectance. <i>Applied Physics Express</i> , <b>2016</b> , 9, 021002	2.4	2
230	Pressure coefficients for direct optical transitions in MoS <sub>2</sub> , MoSe <sub>2</sub> , WS <sub>2</sub> , and WSe <sub>2</sub> crystals and semiconductor to metal transitions. <i>Scientific Reports</i> , <b>2016</b> , 6, 26663	4.9	44
229	Material gain engineering in GeSn/Ge quantum wells integrated with an Si platform. <i>Scientific Reports</i> , <b>2016</b> , 6, 34082	4.9	39
228	Sensitivity of Fermi level position at Ga-polar, N-polar, and nonpolar m-plane GaN surfaces to vacuum and air ambient. <i>Japanese Journal of Applied Physics</i> , <b>2016</b> , 55, 05FA08	1.4	6
227	Temperature dependence of energy gap of Ge <sub>1-x</sub> Sn <sub>x</sub> alloys with x. <i>Journal Physics D: Applied Physics</i> , <b>2016</b> , 49, 235301	3	7



226	The influence of nitrogen and antimony on the optical quality of InNAs(Sb) alloys. <i>Journal Physics D: Applied Physics</i> , <b>2016</b> , 49, 115105	3	7
225	Bi-induced acceptor level responsible for partial compensation of native free electron density in InP $\delta$ Bixdilute bismide alloys. <i>Journal Physics D: Applied Physics</i> , <b>2016</b> , 49, 115107	3	12
224	Origin and annealing of deep-level defects in GaNAs grown by metalorganic vapor phase epitaxy. <i>Journal of Applied Physics</i> , <b>2016</b> , 119, 185706	2.5	7
223	Electromodulation spectroscopy of direct optical transitions in Ge $_{1-x}$ Sn $_x$ layers under hydrostatic pressure and built-in strain. <i>Journal of Applied Physics</i> , <b>2016</b> , 119, 215703	2.5	21
222	Photoacoustic spectroscopy of absorption edge for GaAsBi/GaAs nanowires grown on Si substrate. <i>Applied Physics Letters</i> , <b>2016</b> , 109, 182106	3.4	14
221	Direct optical transitions at K- and H-point of Brillouin zone in bulk MoS $_2$ , MoSe $_2$ , WS $_2$ , and WSe $_2$ . <i>Journal of Applied Physics</i> , <b>2016</b> , 119, 235705	2.5	33
220	Band structure of germanium carbides for direct bandgap silicon photonics. <i>Journal of Applied Physics</i> , <b>2016</b> , 120, 053102	2.5	15
219	Electronic band structure and material gain of III-V-Bi quantum wells grown on GaSb substrate and dedicated for mid-infrared spectral range. <i>Journal of Applied Physics</i> , <b>2016</b> , 119, 075701	2.5	23
218	Engineering of electric field distribution in GaN(cap)/AlGaIn/GaN heterostructures: theoretical and experimental studies. <i>Journal Physics D: Applied Physics</i> , <b>2016</b> , 49, 345106	3	9
217	Effects of a semiconductor matrix on the band anticrossing in dilute group II-VI oxides. <i>Semiconductor Science and Technology</i> , <b>2015</b> , 30, 085018	1.8	14
216	First-principles calculations of bismuth induced changes in the band structure of dilute Ga $\delta$ Bi and In $\delta$ Bi alloys: chemical trends versus experimental data. <i>Semiconductor Science and Technology</i> , <b>2015</b> , 30, 094001	1.8	70
215	Optical absorption and thermal conductivity of GaAsPN absorbers grown on GaP in view of their use in multijunction solar cells. <i>Solar Energy Materials and Solar Cells</i> , <b>2015</b> , 141, 291-298	6.4	19
214	Optical properties of GaAsBi/GaAs quantum wells: Photoreflectance, photoluminescence and time-resolved photoluminescence study. <i>Semiconductor Science and Technology</i> , <b>2015</b> , 30, 094005	1.8	25
213	Ammonothermal growth of GaN crystals on HVPE-GaN seeds prepared with the use of ammonothermal substrates. <i>Journal of Crystal Growth</i> , <b>2015</b> , 427, 1-6	1.6	12
212	Photoluminescence characterization of InGaIn/InGaIn quantum wells grown by plasma-assisted molecular beam epitaxy: Impact of nitrogen and gallium fluxes. <i>Physica Status Solidi (B): Basic Research</i> , <b>2015</b> , 252, 983-988	1.3	1
211	Nitrogen-related changes in exciton localization and dynamics in GaInNAs/GaAs quantum wells grown by metalorganic vapor phase epitaxy. <i>Applied Physics A: Materials Science and Processing</i> , <b>2015</b> , 118, 479-486	2.6	11
210	Electronic band structure of compressively strained Ge $_{1-x}$ Sn $_x$ with x . <i>Applied Physics Letters</i> , <b>2015</b> , 106, 142102	3.4	29
209	Temperature evolution of carrier dynamics in GaN $_x$ PyAs $_{1-x}$ alloys. <i>Journal of Applied Physics</i> , <b>2015</b> , 117, 175702	2.5	15

208	Theoretical and experimental studies of electric field distribution in N-polar GaN/AlGaIn/GaN heterostructures. <i>Applied Physics Letters</i> , <b>2015</b> , 107, 262107	3.4	8
207	8-band and 14-band kp modeling of electronic band structure and material gain in Ga(In)AsBi quantum wells grown on GaAs and InP substrates. <i>Journal of Applied Physics</i> , <b>2015</b> , 118, 055702	2.5	32
206	Contactless electroreflectance studies of surface potential barrier in AlGaIn/n-AlGaIn structures with various Al concentrations. <i>Physica Status Solidi (B): Basic Research</i> , <b>2015</b> , 252, 1038-1042	1.3	1
205	Fourier analysis of scratches generated on m-GaN substrates during polishing. <i>Crystal Research and Technology</i> , <b>2015</b> , 50, 263-267	1.3	2
204	Contactless electroreflectance spectroscopy of ZnO/ZnMgO quantum wells: Optical transitions and Fabry-Pérot features. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2015</b> , 212, 780-784	1.6	8
203	Electronic Band Structure and Material Gain of Dilute Nitride Quantum Wells Grown on InP Substrate. <i>IEEE Journal of Quantum Electronics</i> , <b>2015</b> , 51, 1-12	2	6
202	Simultaneous growth of GaN/AlGaIn quantum wells on c-, a-, m-, and (20.1)-plane GaN bulk substrates obtained by the ammonothermal method: Structural studies. <i>Journal of Crystal Growth</i> , <b>2015</b> , 414, 87-93	1.6	2
201	Influence of quantum well inhomogeneities on absorption, spontaneous emission, photoluminescence decay time, and lasing in polar InGaIn quantum wells emitting in the blue-green spectral region. <i>Applied Physics A: Materials Science and Processing</i> , <b>2014</b> , 115, 1015-1023	2.6	6
200	Optimization of GaInNAs quantum-well vertical-cavity surface-emitting laser emitting at 2.33 $\mu\text{m}$ . <i>Applied Physics A: Materials Science and Processing</i> , <b>2014</b> , 115, 961-969	2.6	2
199	Position of fermi level on Al <sub>0.2</sub> Ga <sub>0.8</sub> N surface and distribution of electric field in Al <sub>0.2</sub> Ga <sub>0.8</sub> N/GaN heterostructures without and with AlN layer. <i>Journal of Applied Physics</i> , <b>2014</b> , 115, 133504	2.5	5
198	Theoretical studies of optical gain tuning by hydrostatic pressure in GaInNAs/GaAs quantum wells. <i>Journal of Applied Physics</i> , <b>2014</b> , 115, 033515	2.5	12
197	Identification of nitrogen- and host-related deep-level traps in n-type GaNAs and their evolution upon annealing. <i>Journal of Applied Physics</i> , <b>2014</b> , 116, 013705	2.5	10
196	Theoretical and experimental studies of electronic band structure for GaSb <sub>1-x</sub> Bi <sub>x</sub> in the dilute Bi regime. <i>Journal Physics D: Applied Physics</i> , <b>2014</b> , 47, 355107	3	46
195	High Bi content GaSbBi alloys. <i>Journal of Applied Physics</i> , <b>2014</b> , 116, 043511	2.5	60
194	Electronic Band Structure of Ga <sub>x</sub> PyAs <sub>1-x</sub> Highly Mismatched Alloys: Suitability for Intermediate-Band Solar Cells. <i>Physical Review Applied</i> , <b>2014</b> , 1,	4.3	60
193	Time-resolved photoluminescence studies of annealed 1.3- $\mu\text{m}$ GaInNAsSb quantum wells. <i>Nanoscale Research Letters</i> , <b>2014</b> , 9, 81	5	11
192	Band anticrossing in ZnOSe highly mismatched alloy. <i>Applied Physics Express</i> , <b>2014</b> , 7, 071202	2.4	19
191	Photorefectance spectroscopy of GaInSbBi and AlGaSbBi quaternary alloys. <i>Applied Physics Letters</i> , <b>2014</b> , 105, 112102	3.4	10



190	Low- and high-energy photoluminescence from GaSb <sub>1-x</sub> Bix with 0 . <i>Applied Physics Express</i> , <b>2014</b> , 7, 1112024	2.4	27
189	Contactless electroreflectance and theoretical studies of band gap and spin-orbit splitting in InP <sub>1-x</sub> Bix dilute bismide with x <sub>0.034</sub> . <i>Applied Physics Letters</i> , <b>2014</b> , 105, 222104	3.4	34
188	Surface photovoltage and modulation spectroscopy of E <sub>1</sub> and E <sub>1</sub> <sup>+</sup> transitions in GaNAs layers. <i>Thin Solid Films</i> , <b>2014</b> , 567, 101-104	2.2	14
187	. <i>IEEE Journal of Quantum Electronics</i> , <b>2014</b> , 50, 1-10	2	5
186	Atomic force microscopy of partially polished and epi-ready c-plane GaN substrates obtained by an ammonothermal method. <i>Applied Physics Express</i> , <b>2014</b> , 7, 055504	2.4	4
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62	Photoluminescence from InAsN quantum dots embedded in GaInNAs/GaAs quantum wells. <i>Journal of Applied Physics</i> , <b>2007</b> , 101, 113539	2.5	4
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55	Photoreflectance investigation of InAs quantum dashes embedded in $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}/\text{In}_{0.53}\text{Ga}_{0.23}\text{Al}_{0.24}\text{As}$ quantum well grown on InP substrate. <i>Applied Physics Letters</i> , <b>2006</b> , 88, 141915	3.4	13
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40	Photo- and Electro-reflectance of III-V-N Compounds and Low Dimensional Structures <b>2005</b> , 279-324		3
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29	Investigation of GaNAsSb/GaAs and GaInNAsSb/GaNAs/GaAs Band Offsets. <i>Materials Research Society Symposia Proceedings</i> , <b>2005</b> , 864, 331		

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